AIGaInP Visible Laser Diode

ADL66502TX/R/L/U

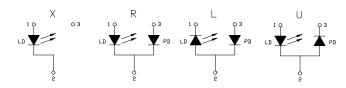
<u>Under Development</u>

660nm 50mW 60°C **Reliable High Power Operation**

Applications

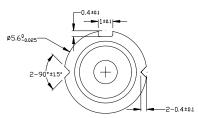
Light source for high power industrial & medical applications

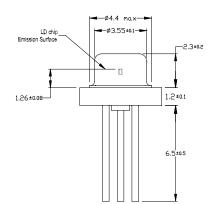
•Pin connections

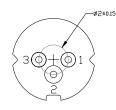


Absolute maximum ratings

Parameter	Symbol	Condition	Rating	Unit
Light output power	P₀	CW	55	mW
Reverse voltage (LD)	V _{RL}	CW	2	V
Reverse voltage (PD)	V _{rd}	-	30	V
Forward current (PD)	I _{FD}	-	10	mA
Case temperature	T _c	CW	-10~+60	°C
Storage temperature	Ts	-	-40~+75	°C







•Electrical and optical characteristics ($T_c=25$ °C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Peak wavelength		650	660	665	nm	
Threshold current	l _{th}	-	45	70	mA	P₀=50mW
Operating current	I _{op}	-	100	120	mA	
Operating voltage	V _{op}	-	2.5	2.8	V	
Differential efficiency		0.7	1.0	1.3	mW/mA	P₀=35-45mW
Monitor current (For TR,TL type)	l _m		0.5	-	mA	P _o =50mW, V _{RD} =5V
Parallel divergence angle	//		9	-	deg	
Perpendicular divergence angle		-	20	-	deg	
Parallel FFP deviation angle		-	-	±2	deg	P₀=50mW
Perpendicular FFP deviation angle		-	-	±2	deg	
Emission point accuracy	хуz	-	-	±80	um	

Precautions

Precation of the device above the maximum rating condition, even momentarily. It may cause unexpected permanent damage to the device.
Semiconductor laser device is very sensitive to electrostatic discharge. High voltage spike current may change the characteristics of the device, or malfunction at any time during its service period. Therefore, proper measures for preventing electrostatic discharge are strongly recommended.
Effective heat sink can help the device operates under a more relax condition; as a result, a more stable characteristics and better reliability can be achieved. So it is

recommended that always apply proper heat sink before the device is operating. 4. Do not look into the laser beam directly by bare eyes. The laser beam may cause severe damage to human eyes.